



S/N 08/902,133

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: George Eckert II

Serial No.: 08/902,133

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.356US1

Title: MEMORY DEVICE

COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS RCE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
08/903452	July 29, 1997	303.324US1	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/256643 6746893	February 23, 1999	303.324US2	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/691004	October 18, 2000	303.324US4	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
08/903486	July 29, 1997	303.326US1	SILICON CARBIDE GATE TRANSISTOR
09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR

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08/902132 5886368	July 29, 1997	303.353US1	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294 6309907	August 21, 1998	303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
08/902843	July 29, 1997	303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/135413	August 14, 1998	303.354US2	METHOD FOR OPERATING A MEMORY DEVICE HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/134713	August 14, 1998	303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
08/902098 6031263	July 29, 1997	303.355US1	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/140978 6307775	August 27, 1998	303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/141392 6249020	August 27, 1998	303.355US3	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/883795	June 18, 2001	303.355US4	METHOD OF FORMING A DEVICE WITH A GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
10/047181	October 23, 2001	303.355US5	MEMORY DEVICE WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE

10/231687	August 29, 2002	303.356US2	MEMORY DEVICE
08/903453	July 29, 1997	303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/258467	February 26, 1999	303.378US2	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/650553 6731531	August 30, 2000	303.378US3	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
10/461593	June 11, 2003	303.356US3	MEMORY DEVICE
10/789203	February 27, 2004	303.356US4	OPERATING A MEMORY DEVICE

Respectfully submitted,

LEONARD FORBES ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 371-2157

Date 18 June 2004 By David R. Cochran
David R. Cochran
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 18th day of June, 2004.

Name Amy Moriarty

Signature Amy Moriarty